

Fig.1

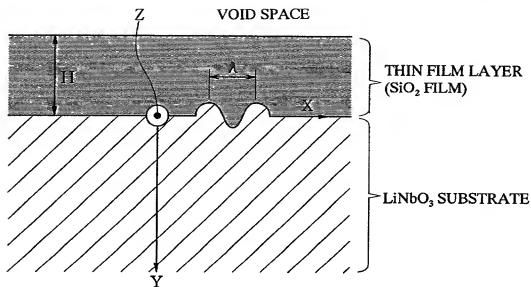
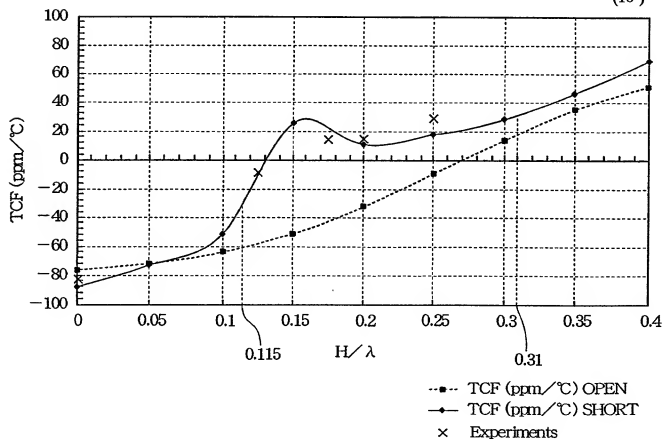


Fig.2
(10°)



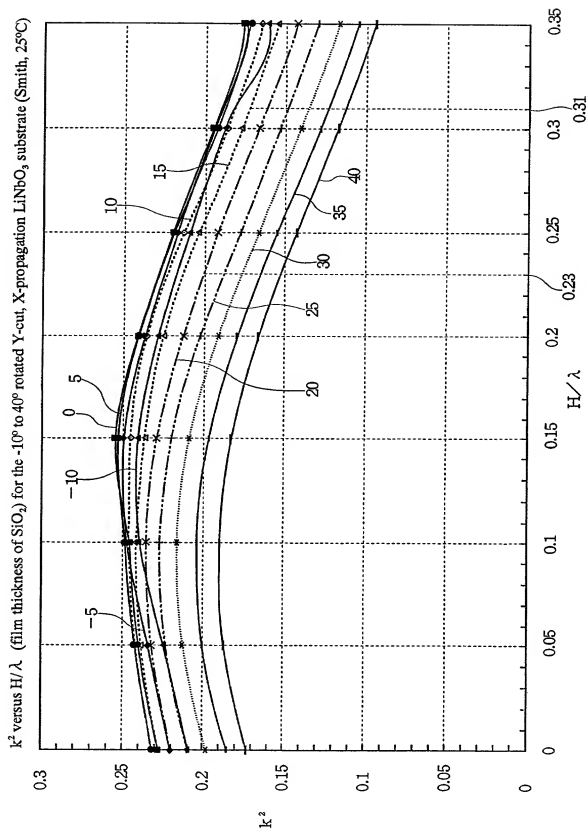


Fig.3

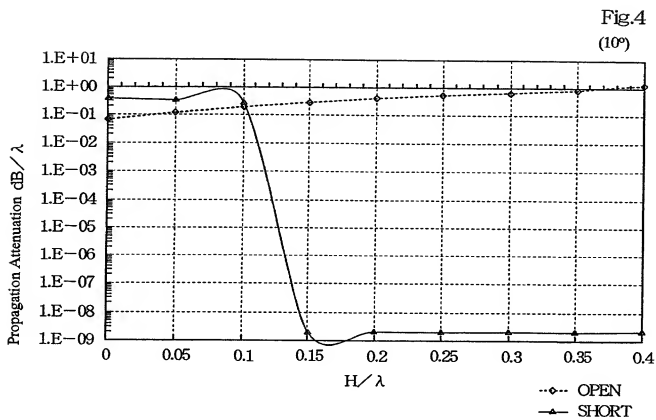


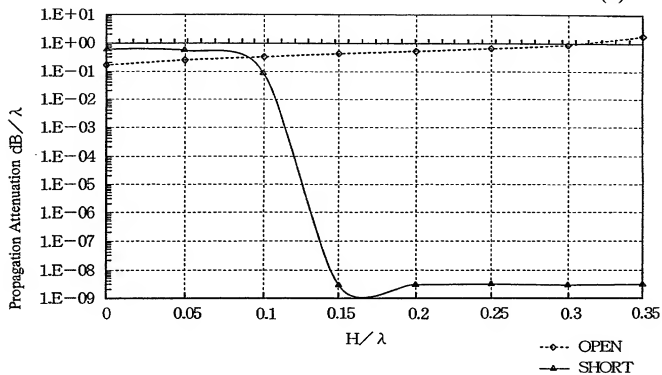
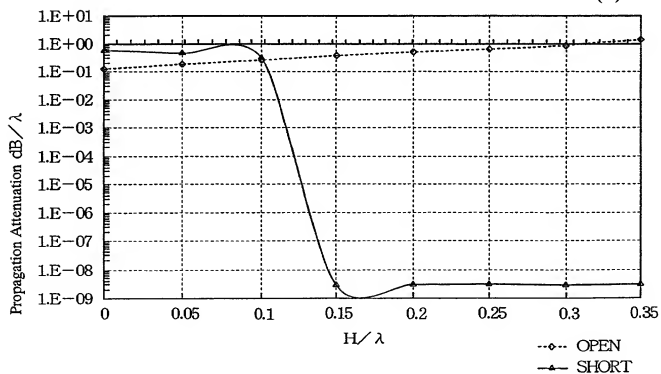
Fig.5
(0°)Fig.6
(5°)

Fig.7
(10°)

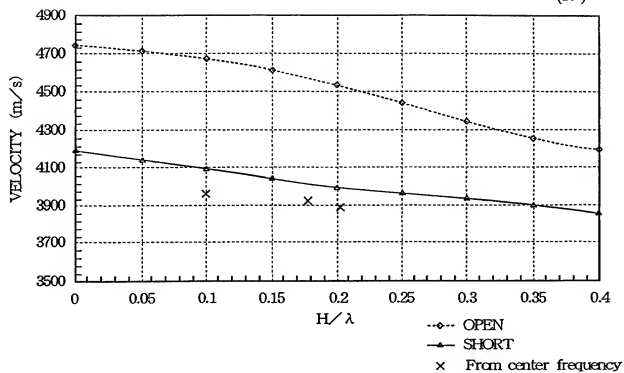


Fig.8

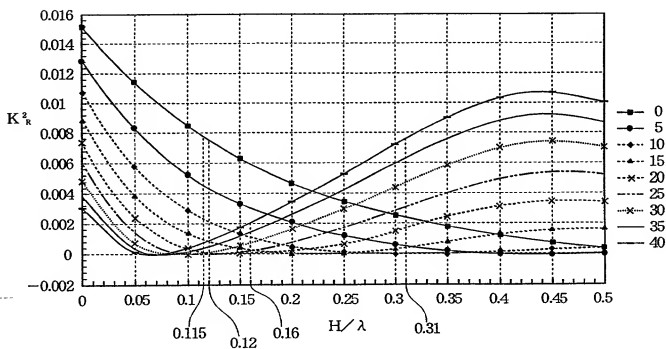
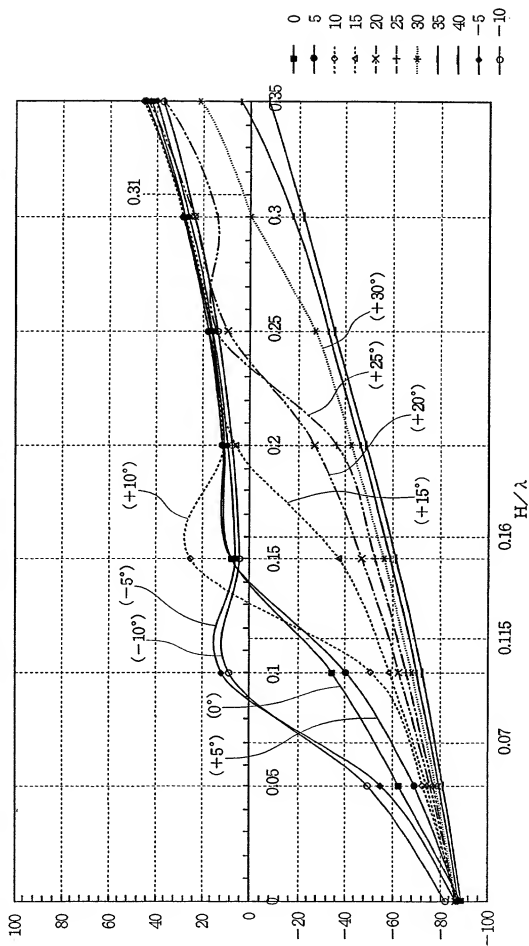


Fig.9

TCF (ppm/°C) versus H/λ (film thickness of SiO_2) for SHORT of the 0° to 40° rotated Y-cut, X-propagation LiNbO_3 substrate (Smith constant)

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Fig.10

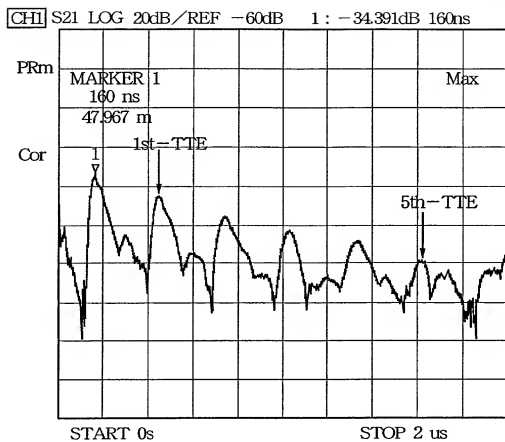


Fig.11

